NSN 5961-00-493-0401

Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-493-0401 **Inclosure Material:** Metal **Overall Length:** 0.365 inches **Overall Diameter:** 0.503 inches **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Gate **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 50.0 breakover voltage, dc **Current Rating Per Characteristic:** 7.00 amperes source cutoff current **Power Rating Per Characteristic:** 0.5 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 100.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpn **Terminal Type And Quantity:** 2 tab, solder lug and 1 case **Specification Data:** 80131-release5700 professional/industrial association specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0